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MOS FIELD EFFECT POWER TRANSISTOR 2SK1992/2SK1993

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

The 2SK1992/2SK1993 is N-channel MOS Field Effect Transistor designed for high voltage switching applications.

FEATURES

- Low On-state Resistance
 $R_{DS(on)} \leq 0.9/1.0 \Omega$ ($V_{GS} = 10 V, I_D = 3.0 A$)
- Low C_{iss} $C_{iss} = 1\ 060\ pF$ TYP.
- Built-in G-S Gate Protection Diode
- High Avalanche Capability Ratings

QUALITY GRADE

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

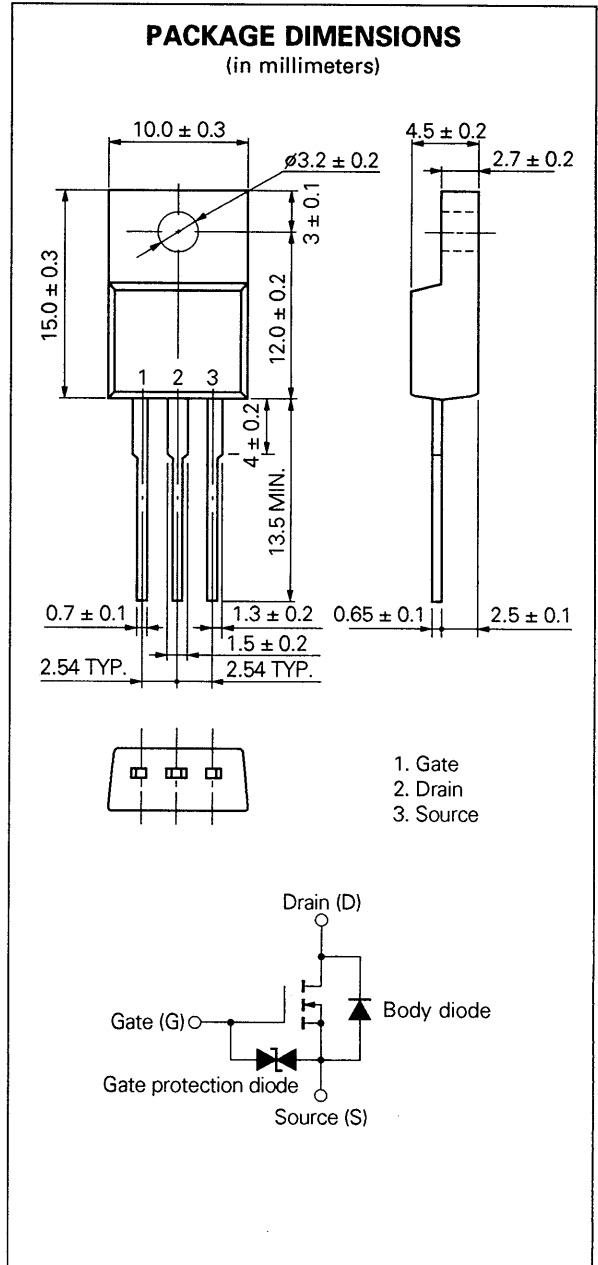
ABSOLUTE MAXIMUM RATINGS ($T_a = 25\ ^\circ C$)

Drain to Source Voltage	V_{DSS}	450/500	V
Gate to Source Voltage	V_{GSS}	± 30	V
Drain Current (DC)	$I_{D(DC)}$	± 6.0	A
Drain Current (pulse)	$I_{D(pulse)^*}$	± 24	A
Total Power Dissipation ($T_c = 25\ ^\circ C$)	P_{T1}	35	W
Total Power Dissipation ($T_a = 25\ ^\circ C$)	P_{T2}	2.0	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$
Single Avalanche Current	I_{AS}^{**}	9.0	A
Single Avalanche Energy	E_{AS}^{**}	243	mJ

* $PW \leq 10\ \mu s$, Duty Cycle $\leq 1\ %$

** Starting $T_{ch} = 25\ ^\circ C$, $R_G = 25\ \Omega$, $V_{GS} = 20\ V \rightarrow 0$

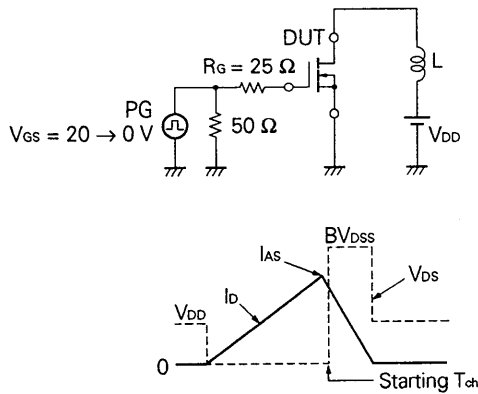
PACKAGE DIMENSIONS (in millimeters)



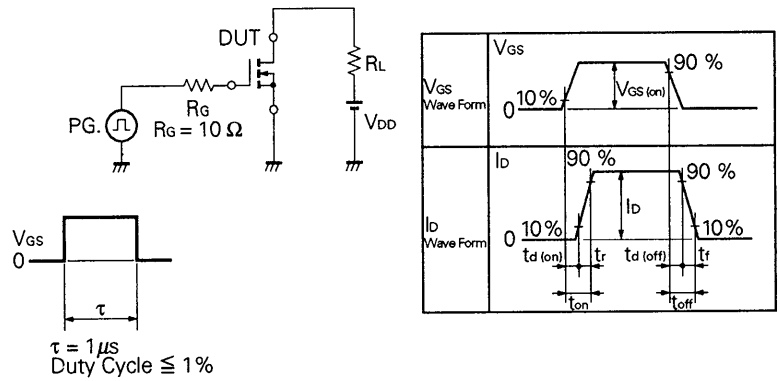
ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-state Resistance (2SK1992)	R _{DS(on)}		0.7	0.9	Ω	V _{GS} = 10 V, I _b = 3.0 A
Drain to Source On-state Resistance (2SK1993)			0.8	1.0	Ω	V _{GS} = 10 V, I _b = 3.0 A
Gate to Source Cutoff Voltage	V _{GS(off)}	2.5		3.5	V	V _{DS} = 10 V, I _b = 1 mA
Forward Transfer Admittance	y _{fs}	2.8			S	V _{DS} = 10 V, I _b = 3.0 A
Drain Leakage Current (2SK1992/1993)	I _{DSS}			100	μA	V _{DS} = 450/500 V, V _{GS} = 0
Gate to Source Leakage Current	I _{GSS}			±10	μA	V _{GS} = ±30 V, V _{DS} = 0
Input Capacitance	C _{iss}		1 060		pF	V _{DS} = 10 V V _{GS} = 0 f = 1 MHz
Output Capacitance	C _{oss}		340		pF	
Reverse Transfer Capacitance	C _{rss}		150		pF	
Turn-On Delay Time	t _{d(on)}		20		ns	V _{GS} = 10 V V _{DD} = 150 V I _b = 3.0 A, R _G = 10 Ω R _L = 50 Ω
Rise Time	t _r		30		ns	
Turn-Off Delay Time	t _{d(off)}		70		ns	
Fall Time	t _f		20		ns	
Total Gate Charge	Q _G		36		nC	V _{GS} = 10 V I _b = 6 A V _{DD} = 400 V
Gate to Source Charge	Q _{GS}		7		nC	
Gate to Drain Charge	Q _{GD}		21		nC	
Diode Forward Voltage	V _{F(S-D)}		0.9		V	I _F = 6 A, V _{GS} = 0
Reverse Recovery Time	t _{rr}		420		ns	I _F = 6 A
Reverse Recovery Charge	Q _{rr}		2.0		μC	di/dt = 50 A/μs

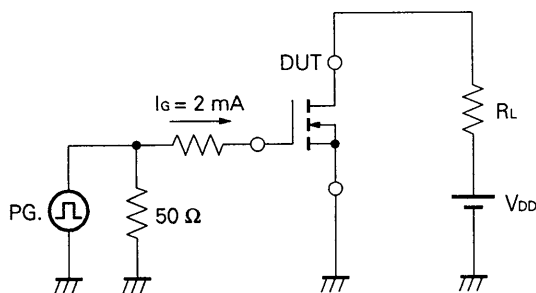
Test Circuit 1: Avalanche Capability



Test Circuit 2: Switching Time

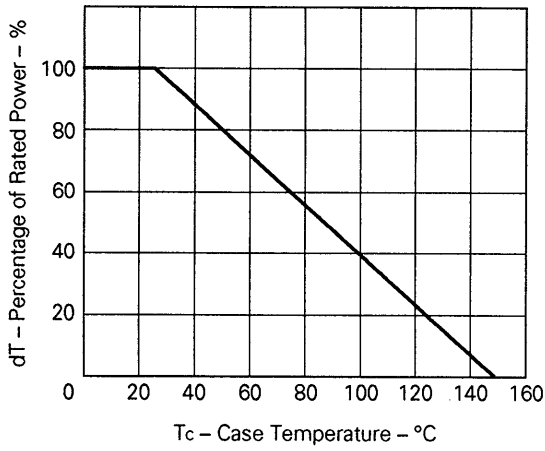


Test Circuit 3: Gate Charge

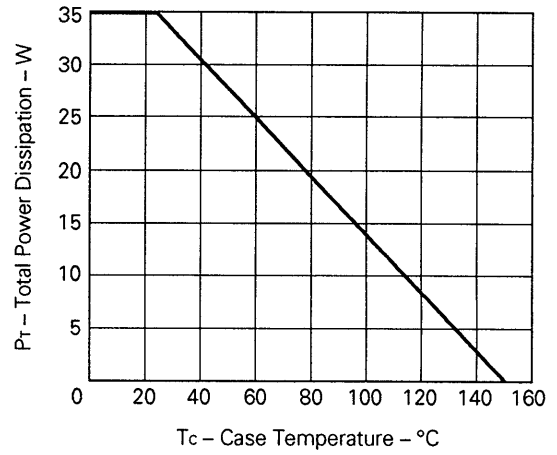


TYPICAL CHARACTERISTICS (T_a = 25 °C)

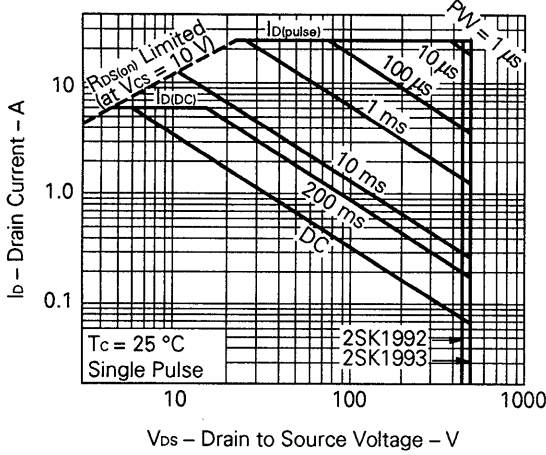
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



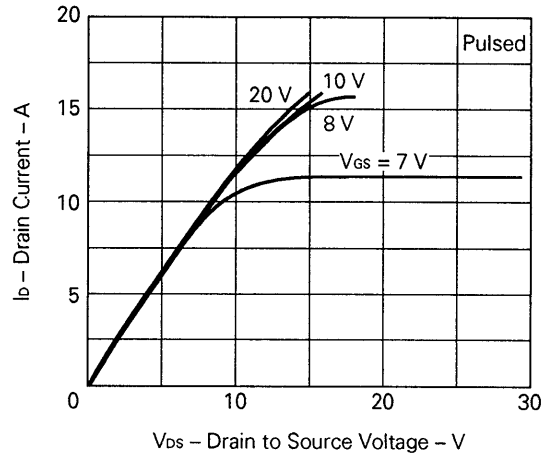
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



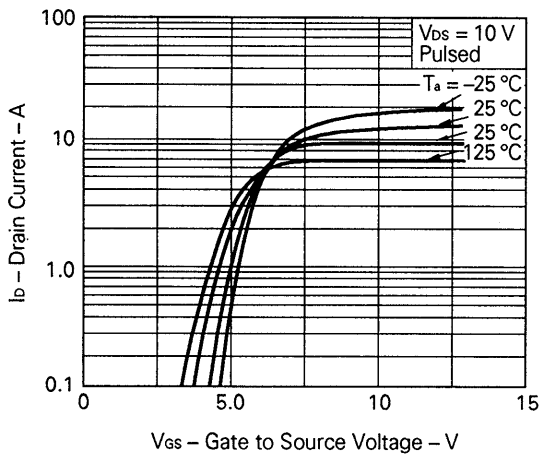
FORWARD BIAS SAFE OPERATING AREA



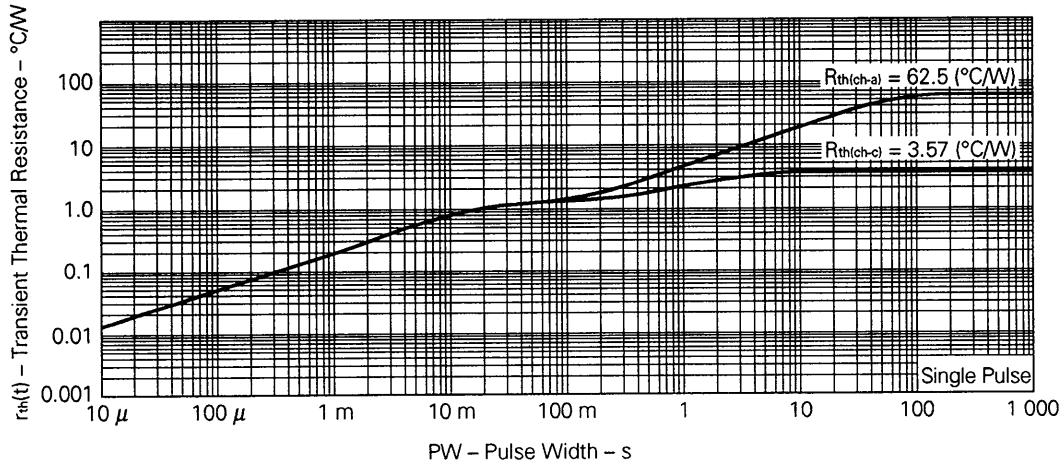
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



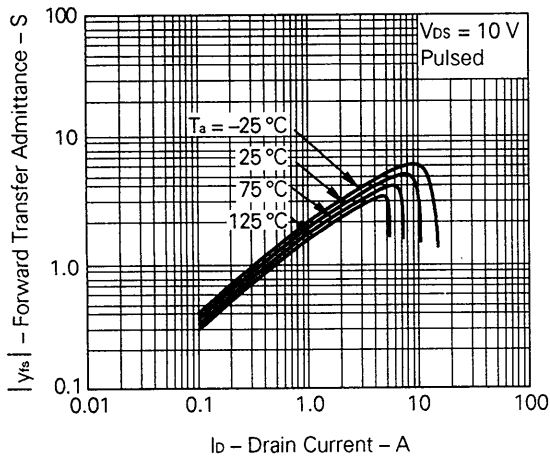
TRANSFER CHARACTERISTICS



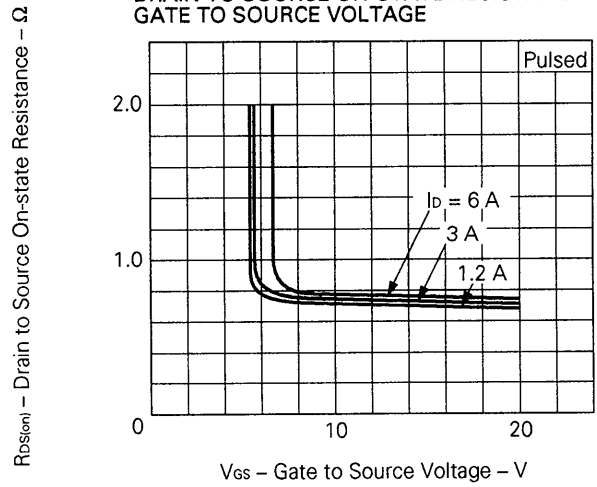
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



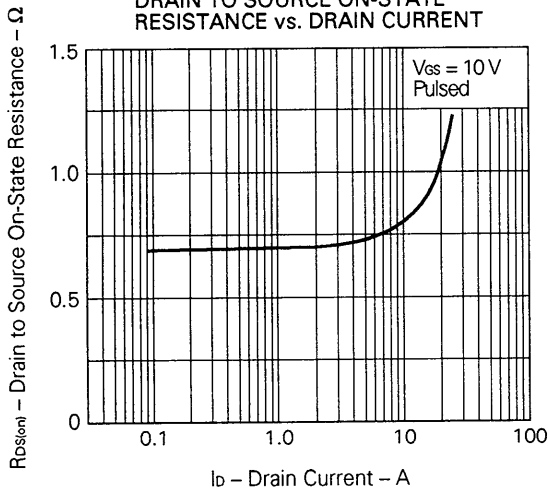
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



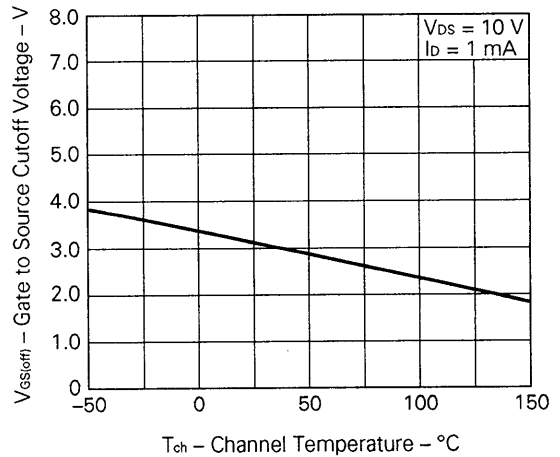
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



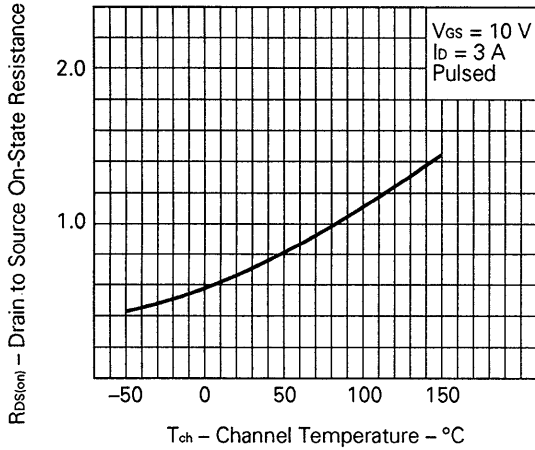
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



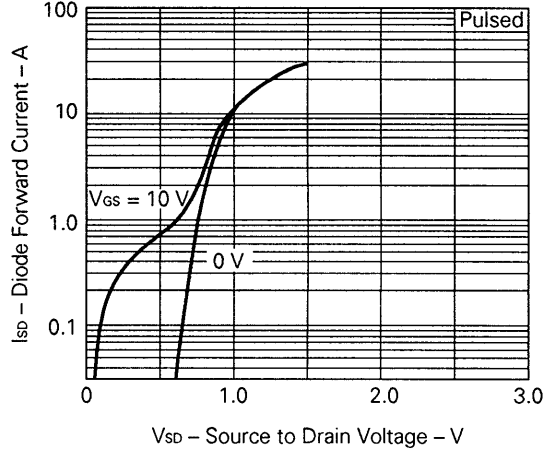
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



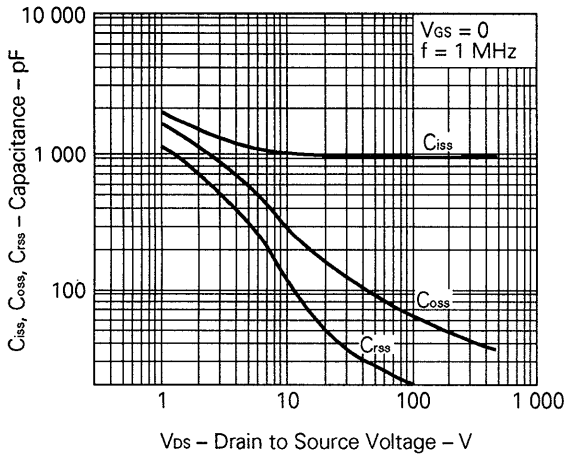
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



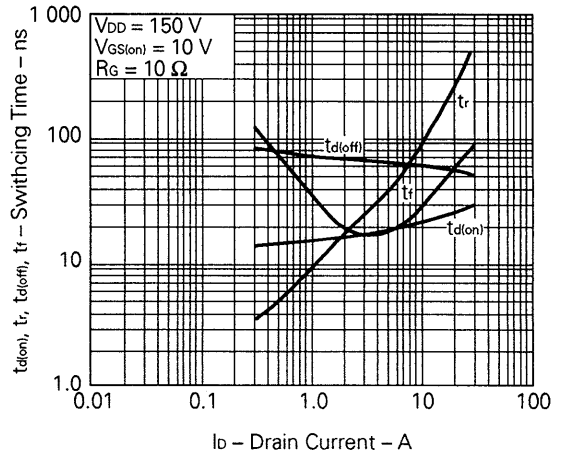
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



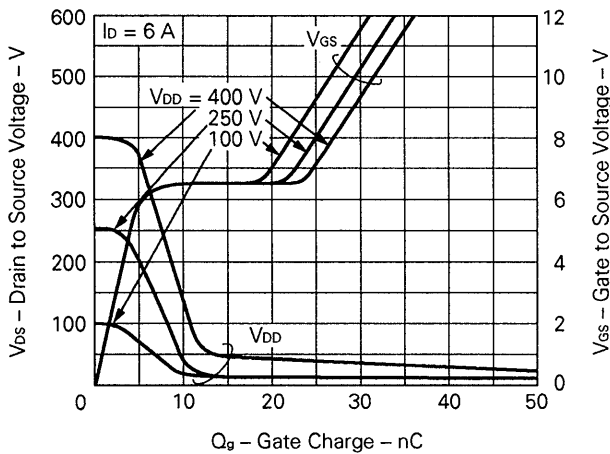
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



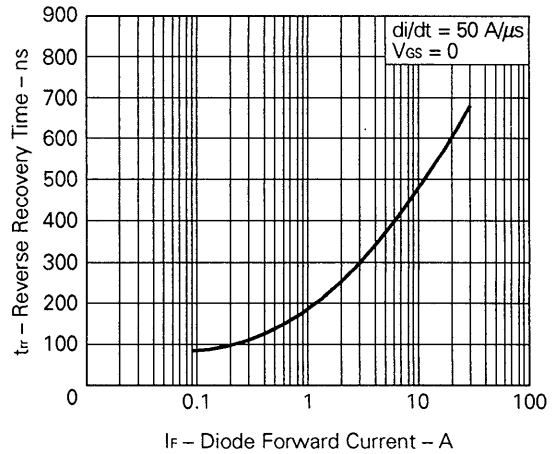
SWITCHING CHARACTERISTICS

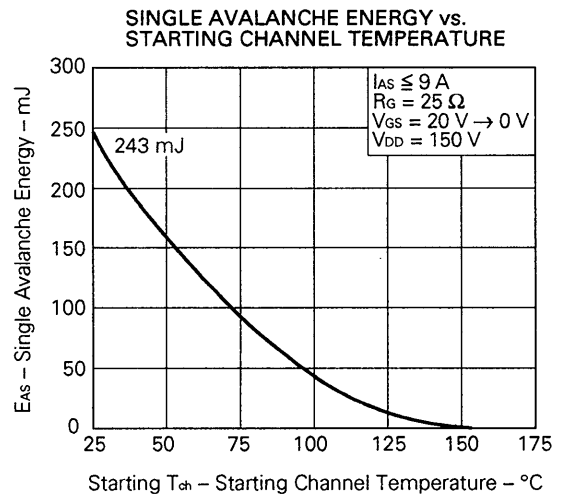
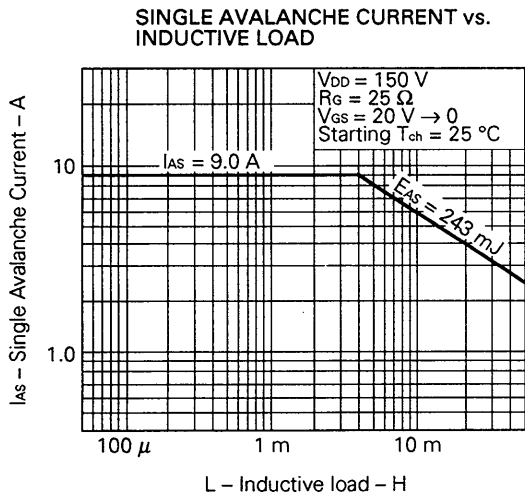


DYNAMIC INPUT CHARACTERISTICS



REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT





Reference

Application note name	No.
Safe operating area of Power MOS FET.	TEA-1034
Application circuit using Power MOS FET.	TEA-1035
Quality control of NEC semiconductors devices.	TEI-1202
Quality control guide of semiconductors devices.	MEI-1202
Assembly manual of semiconductors devices.	IEI-1207

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